

File Number **523****2N6249, 2N6250, 2N6251**

450-V, 30-A, 175-W Silicon N-P-N Switching Transistors

For Switching Applications in Industrial and Commercial Equipment

Features:

- **High voltage ratings:**
 $V_{CE0} = 450\text{ V (2N6251)}$
 375 V (2N6250)
 300 V (2N6249)
- **High dissipation rating:**
 $P_T = 175\text{ W}$
- **Low saturation voltages**
- **Maximum safe-area-of-operation curves**

RCA-2N6249, 2N6250 and 2N6251 are multiple epitaxial silicon n-p-n power transistors. Multiple-epitaxial construction maximizes the volt-ampere characteristic of the device and provides fast switching speeds.

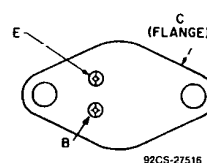
These devices use the popular JEDEC TO-204AA package; they differ mainly in voltage ratings, leakage-current limits, and $V_{CE(sat)}$ ratings.

The exceptional second-breakdown capabilities and high voltage-breakdown ratings make these transistors especially suitable for offline inverters, switching regulators motor controls, and deflection circuit applications.

The high gain and high $E_{s/b}$ energy-handling capability of the 2N6249 make it an excellent choice for motor-control applications in which large winding inductances are encountered and high surge currents are required to start the motor.

The high breakdown voltages, low saturation voltages, and fast-switching capability of the 2N6250 and 2N6251 make them especially suitable for inverter circuits operating directly off the rectified 115-V power line or a bridge configuration operating from the rectified 220-V line.

TERMINAL DESIGNATIONS



JEDEC TO-213AA

MAXIMUM RATINGS, Absolute-Maximum Values:

	2N6249	2N6250	2N6251	
* V_{CE0}	300	375	450	V
$V_{CE0(sus)}$	200	275	350	V
* $V_{CEX(sus)}$ ($V_{BE} = 0\text{ V}$)	225	300	375	V
$V_{CEX(sus)}$ ($R_{BE} \leq 50\ \Omega$)	225	300	375	V
* V_{EBO}	6	6	6	V
* I_C	10	10	10	A
I_{CM}	30	30	30	A
* I_B	10	10	10	A
* P_T				W
At T_C up to 25°C and V_{CE} up to 30 V	175	175	175	
At T_C up to 25°C and V_{CE} above 30 V	Derate Linearly at 1 _____			$^\circ\text{C/W}$
* T_J, T_{stg}	-65 to +200			$^\circ\text{C}$
* T_L				$^\circ\text{C}$
At distances $\geq 1/32\text{ in. (0.8 mm)}$ from case for 10 s max.	230			

* 2N-Series types in accordance with JEDEC registration data format (JS-6, RDF-1).

High-Voltage Power Transistors

2N6249, 2N6250, 2N6251

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C Unless Otherwise Specified

CHARACTERISTIC	TEST CONDITIONS			LIMITS									UNITS
	DC VOLTAGE (V)	DC CURRENT (A)		2N6249			2N6250			2N6251			
		V _{CE}	I _C	I _B	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	MIN.	TYP.	
I _{CEO}	150 225 300		0 0 0	— — —	— — —	5 — —	— — —	— — —	5 — —	— — —	— — —	5 — —	mA
I _{CEV} V _{BE} = -1.5	225 300 375			— — —	— — —	5 — —	— — —	— — —	5 — —	— — —	— — —	5 — —	
I _{CEV} V _{BE} = -1.5 T _C = 125°C	225 300 375			— — —	— — —	10 — —	— — —	— — —	10 — —	— — —	— — —	10 — —	
I _{EBO} V _{BE} = -6				— — —	— — —	1 — —	— — —	— — —	1 — —	— — —	— — —	1 — —	
V _{CEO(sus)}	*	0.2		200 ^b	—	—	275 ^b	—	—	350 ^b	—	—	V
V _{CER(sus)} R _{BE} = 50 Ω		0.2		225 ^b	—	—	300 ^b	—	—	375 ^b	—	—	V
V _{EBO} I _E = 1 mA				6	—	—	6	—	—	6	—	—	V
h _{FE}	3	10 ^a		10	—	50	—	—	—	—	—	—	
	3	10 ^a		—	—	—	8	—	50	—	—	—	
	3	10 ^a		—	—	—	—	—	—	6	—	50	
V _{BE(sat)}		10 ^a	1	—	—	2.25	—	—	—	—	—	—	V
		10 ^a	1.25	—	—	—	—	—	2.25	—	—	—	
		10 ^a	1.67	—	—	—	—	—	—	—	—	2.25	
V _{CE(sat)}		10 ^a	1	—	—	1.5	—	—	—	—	—	—	V
		10 ^a	1.25	—	—	—	—	—	1.5	—	—	—	
		10 ^a	1.67	—	—	—	—	—	—	—	—	1.5	
h _{fe} f = 1 MHz	10	1		2.5	8	—	2.5	8	—	2.5	8	—	
I _S /b t _p = 1s nonrep.	30			5.8	—	—	5.8	—	—	5.8	—	—	A
E _S /b V _{BE} = -4 R _B = 50 Ω, L = 50 μH		10 ^c		2.5	—	—	2.5	—	—	2.5	—	—	mJ
t _r V _{CC} = 200 V, I _{B1} = -I _{B2}		10	1	—	0.8	2	—	—	—	—	—	—	μs
		10	1.25	—	—	—	—	0.8	2	—	—	—	
		10	1.67	—	—	—	—	—	—	—	0.8	2	
t _s V _{CC} = 200 V, I _{B1} = -I _{B2}		10	1	—	1.8	3.5	—	—	—	—	—	—	
		10	1.25	—	—	—	—	1.8	3.5	—	—	—	
		10	1.67	—	—	—	—	—	—	—	1.8	3.5	
t _f V _{CC} = 200 V, I _{B1} = -I _{B2}		10	1	—	0.5	1	—	—	—	—	—	—	
		10	1.25	—	—	—	—	0.5	1	—	—	—	
		10	1.67	—	—	—	—	—	—	—	0.5	1	
R _{θJC}	10	5		—	—	1	—	—	1	—	—	1	°C/W

* 2N-Series types in accordance with JEDEC registration data format (JS-6 RDF-1).

^a Pulsed; pulse duration $\leq 300\ \mu\text{s}$, duty factor = 2%.^b CAUTION: The sustaining voltages $V_{CEO(sus)}$ and $V_{CER(sus)}$ MUST NOT be measured on a curve tracer.

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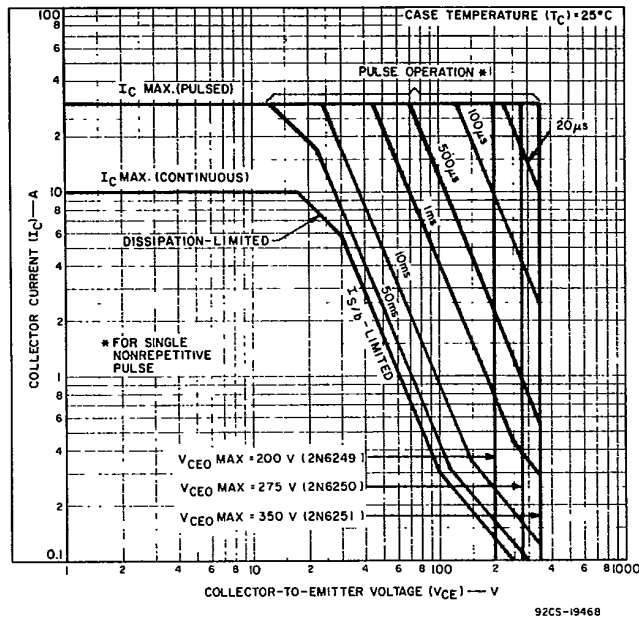


Fig. 1 - Maximum operating areas for all types at $T_c = 25^\circ\text{C}$.

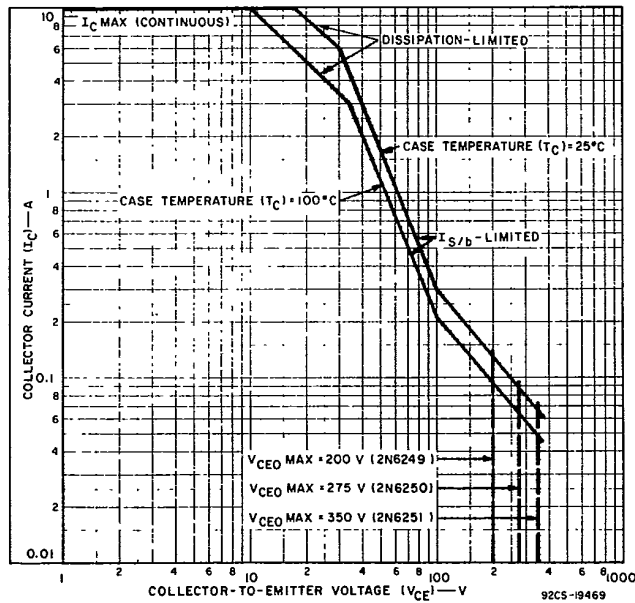


Fig. 2 - Maximum operating areas for all types at $T_c = 100^\circ\text{C}$.

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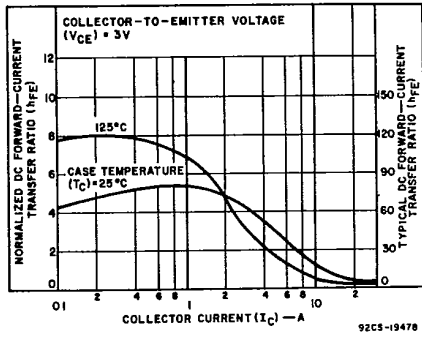


Fig. 3 - Typical normalized dc beta characteristics for all types.

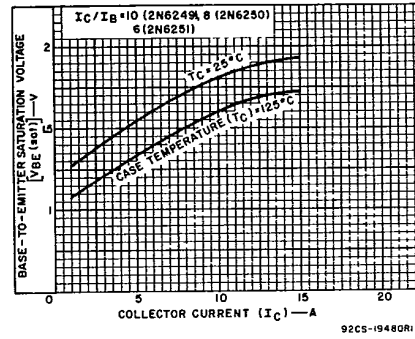


Fig. 4 - Typical base-to-emitter saturation voltage characteristics for all types.

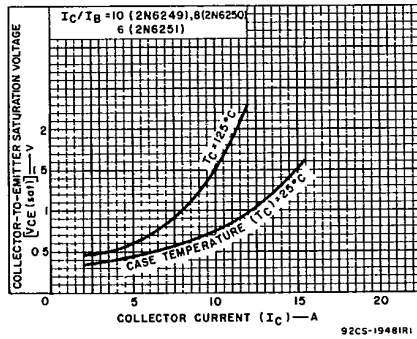


Fig. 5 - Typical collector-to-emitter saturation voltage characteristics for all types.

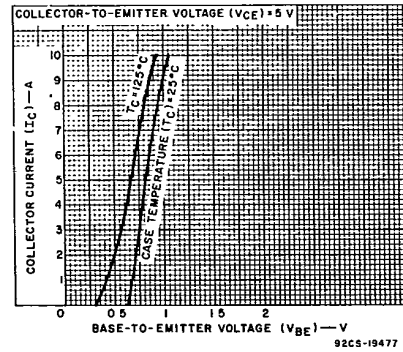


Fig. 6 - Typical transfer characteristics for all types.

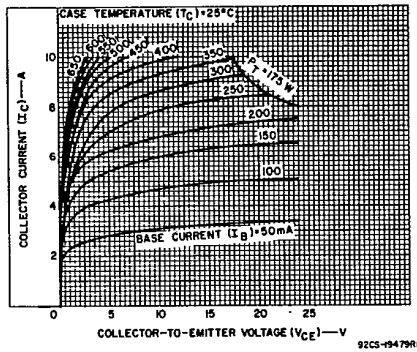


Fig. 7 - Typical output characteristics for all types.

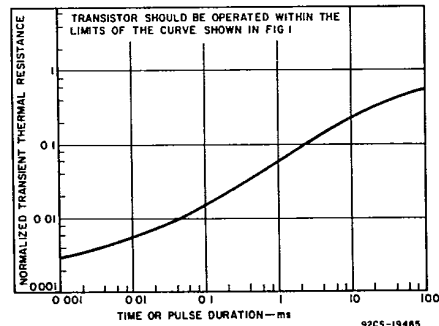


Fig. 8 - Typical thermal response characteristics for all types.

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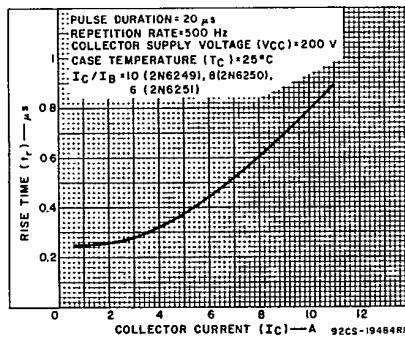


Fig. 9 - Typical rise-time characteristics for all types.

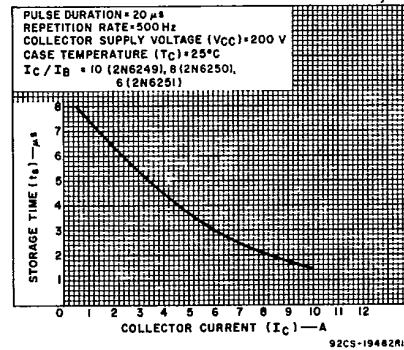


Fig. 10 - Typical storage-time characteristics for all types (with constant forced gain).

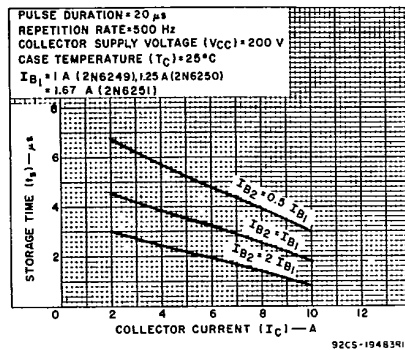


Fig. 11 - Typical storage-time characteristics for all types (with constant base drive).

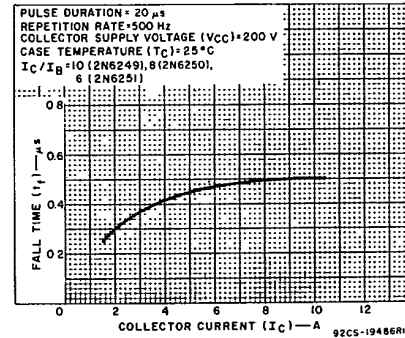


Fig. 12 - Typical fall-time characteristic for all types.

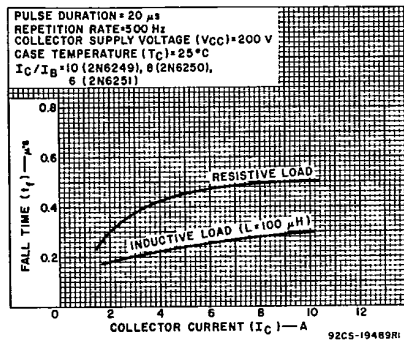


Fig. 13 - Typical inductive- and resistive-load fall-time characteristics for all types.

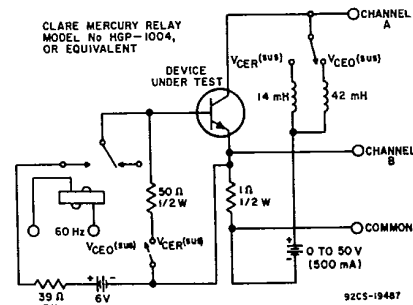
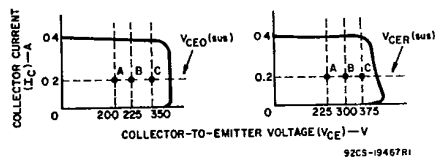


Fig. 14 - Circuit used to measure sustaining voltage $V_{CE0(sus)}$ and $V_{CEr(sus)}$ for all types.

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The sustaining voltages $V_{CEO(sus)}$ and $V_{CER(sus)}$ are acceptable when the traces fall to the right of point "A" for type 2N6249, point "B" for type 2N6250, and point "C" for type 2N6251 ($I_C = 0.2$ A).

Fig. 15 - Oscilloscope display for measurement of sustaining voltages.

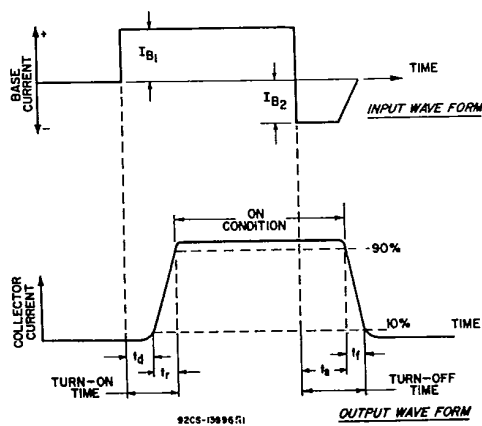


Fig. 17 - Phase relationship between input and output currents showing reference points for specifications of switching times.

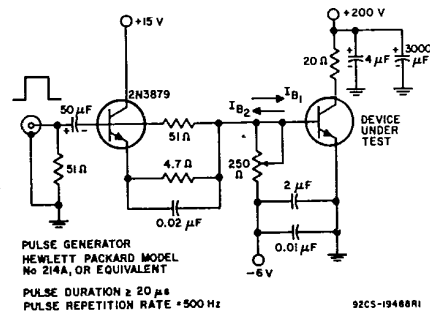


Fig. 16 - Circuit used to measure switching times for all types.

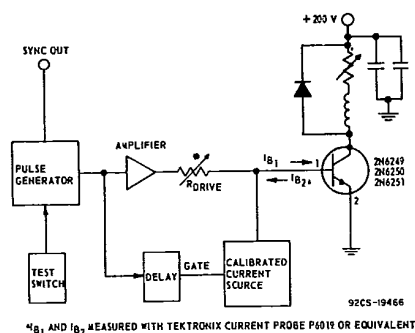


Fig. 18 - Circuit used to measure inductive-load switching times for all types.